

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S38	20	implant\$6 near16 (gan or gallium near2 nitride) near16 separat\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/26 18:33
S37	364	implant\$6 near16 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/26 18:33
S1	35	(si or silicon near2 wafer) near15 (bmd and cop)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 11:32
L2	29	separat\$6 near10 substrate and (gaN or gallium near2 nitride) near15 self\$1support\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 11:34
L3	7	spontaneous\$6 near15 separat\$6 near10 substrate and implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 11:43
L1	7	spontaneous\$6 near15 separat\$6 near10 substrate and (gaN or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 11:43
L8	7	cool\$6 near16 separat\$6 near10 substrate near17 implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 12:02
L6	814	heat near2 treat\$6 near16 separat\$6 near10 substrate near17implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 12:02
L5	178	heat near2 treat\$6 near16 separat\$6 near10 substrate same implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 12:02

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L4	3	spontaneous\$6 near15 separat\$6 near10 substrate same implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 12:02
L9	2	"5374564".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 12:05
L10	2	(ambient or room) near5 temperature near16 separat\$6 near10 substrate near17 implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 12:29
L7	117	heat near2 treat\$6 near16 separat\$6 near10 substrate near17 implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 12:29
L11	479	(ambient or room) near5 temperature near16 separat\$6 near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 12:30
L12	42	11 and (gan or gallium near2 nitride or "iii-V")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 14:13
L13	0	"6303405".pn. and implant\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 14:17
L15	33	ogawa.in. and Group near2 iii near6 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 14:42
L14	20	(gan or gallium near2 nitride) near15 implant\$7 near17 separat\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 14:42
L17	1	"20030077885".pn. and separat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 15:36

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L16	11	ogawa.in. and Group near2 iii near6 substrate and implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 15:36
S24	20	(hacene near2 lahreche or gilles near2 nataf or bernard near2 beaumont).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 15:58
L18	23	(hacene near2 lahreche or gilles near2 nataf or bernard near2 beaumont).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 15:58